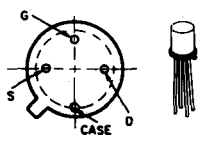
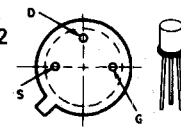



**(Observe MOS Handling) ▲**

ECG Type	Description and Application	Transconductance $g_{fs}$ $\mu$ mhos	Gate to Source Cutoff Voltage $V_{GS}$ (off) Max V	Zero-Gate Drain Current $I_{DSS}$	Drain Current $I_D$	Input Cap $C_{iss}$ Max pf	Gate to Source Breakdown Voltage $BV_{GSS}$ Min V	Drain to Source Resistance $r_{DS}$ (on) Max ohms	Device Diss. PD Max mW	Package
										Case / Fig. / Basing
ECG464 ▲	MOSFET, P-Ch, Enhancement, Sw (Compl to ECG465)	1,000 Min	5	10 nA Max	3 mA Min (on)	5	25	600	300	TO-72 Fig. T4 
						td 60 ns; tr 65 ns; t(off) 60 ns				
ECG465 ▲	MOSFET, N-Ch, Enhancement, Sw (Compl to ECG464)	1,000 Min	5	10 nA Max	3 mA Min (on)	5	25	300	300	
						td 60 ns; tr 65 ns; t(off) 60 ns				
ECG466	JFET, N-Ch, Chopper/Sw.	---	10	50 mA Min	250 pA Max (off)	18	40	25	360	TO-18 Fig. T2 
						td 6 ns; tr 3 ns; t(off) 25 ns				
ECG467	JFET, N-Ch, Chopper/Fast Sw	---	---	50 mA Min	1.0 nA Max (off)	10	30	30	310	TO-92 Fig. T16
						td 4 ns; tr 5 ns; t(off) 5 ns				
ECG468	JFET, N-Ch, Chopper/Sw	8,000	10	20 mA Min	1.0 nA Max (off)	16	35	30	360	
						td 7 ns; tr 6 ns; t(off) 20 ns				
ECG469	JFET, N-Ch, Chopper/Sw.	7,500	3	2 mA Min	1.0 nA Max (off)	16	35	100	360	
						td 7 ns; tr 6 ns; t(off) 20 ns				
ECG490 ▲	MOSFET, N-Ch, Enhancement, Hi Speed, Sw	200,000	3	.5 $\mu$ A	.5 A Max	40	15	5	830	Note: ECG490 Basing is D,G,S.
						td (off) = 10 ns, td (on) = 10 ns, $BV_{DSS} = 60$ V				

▲ Refer to MOSFET Handling Precautions - Page 1-31

Package Outlines - See Page 1-78